Vishay Siliconix

Low Voltage, Dual SPDT Analog Switch with Charge Pump

DESCRIPTION

SHA

The DG2616, DG2617, DG2618 are monolithic CMOS analog switching products designed for high performance switching of analog signals. Combining low power, high speed, low on-resistance and small physical size, the DG2616, DG2617, DG2618 are ideal for portable and battery powered applications.

The DG2616, DG2617, DG2618 have built-in charge-pump circuitry which lowers the minimum supply voltage to + 1.5 V while maintaining low on-resistance. The Control circuitry allows the DG2616, DG2617, DG2618 to operate in different configurations.

Built on Vishay Siliconix's low voltage process, the DG2616, DG2617, DG2618 has an epitaxial layer that prevents latch-up. Break-before-make is guaranteed.

The DG2616, DG2617, DG2618 are manufactured in space saving DFN-10 ($3.0 \times 3.0 \text{ mm}$). And as a committed partner to the community and the environment, Vishay Siliconix manufactures this product with lead (Pb)-free device terminations and is 100 % RoHS compliant.

FEATURES

- Low voltage operation (1.5 V to 3.6 V)
- Low on-resistance R_{ON} : 4.2 Ω typ. at 2.7 V
 - Fast switching: $t_{ON} = 39 \text{ ns}$ $t_{OFF} = 8 \text{ ns}$
- DFN-10 package

BENEFITS

- Reduced power consumption
- High accuracy
- Reduce board space
- TTL/1.8 V logic compatible
- High bandwidth

APPLICATIONS

- Cellular phones
- Audio and video signal routing
- PCMCIA cards
- · Battery operated systems

FUNCTIONAL BLOCK DIAGRAM AND PIN CONFIGURATION

TRUTH TABLE DG2616						
Logic	ogic NC1, 2 NO1, 2					
0	ON	OFF				
1	OFF	ON				

TRUTH TABLE DG2617										
SHDN/EN Logic	SHDN/EN Logic IN Logic NC1, 2 NO1, 2 Charge Pu									
0	0	ON	OFF	ON						
0	1	OFF	ON	ON						
1	0	ON	OFF	OFF						
1	1	OFF	ON	OFF						

TRUTH TABLE DG2618							
SHDN/EN Logic	SHDN/EN Logic IN Logic NC1, 2 NO1,						
0	0	ON	OFF	ON			
0	1	OFF	ON	ON			
1	х	OFF	OFF	OFF			

ORDERING INFORMATION					
Temp. Range	Package Part Number				
- 40 °C to 85 °C	DFN-10	DG2616DN-T1-E4 DG2617DN-T1-E4 DG2618DN-T1-E4			



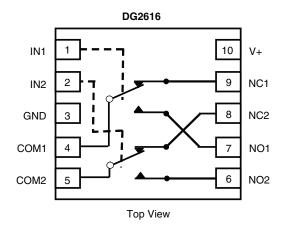
RoHS

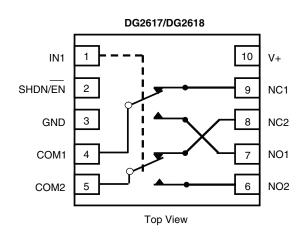
COMPLIANT



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ABSOLUTE MAXIMUM RAT	INGS $T_A = 25 \circ C$, unless other	wise noted		
Parameter		Limit	Unit	
Reference to GND	V+	- 0.3 to 6.0	V	
Reference to GND	IN, COM, NC, NO ^a	- 0.3 to (V+ + 0.3)	v	
Current (Any terminal except NO, NC or C	OM)	30		
Continuous Current (NO, NC, or COM)		± 150	mA	
Peak Current (Pulsed at 1 ms, 10 % Duty Cycle)		± 300		
Storage Temperature (D-Suffix)		- 65 to 150	°C	
Package Solder Reflow Conditions ^d			-0	
Power Dissipation (Packages) ^b	DFN-10 ^c	1191	mW	

Notes:

a. Signals on NC, NO, or COM or IN exceeding V+ will be clamped by internal diodes. Limit forward diode current to maximum current ratings.

b. All leads welded or soldered to PC board.

c. Derate 14.9 mW/°C above 70 °C

d. Manual soldering with iron is not recommended for leadless components. The DFN-10 is a leadless package. The end of the lead terminal is exposed copper (not plated) as a result of the singulation process in manufacturing. A solder fillet at the exposed copper lip cannot be guaranteed and is not required to ensure adequate bottom side solder interconnection.



DG2616, DG2617, DG2618 Vishay Siliconix

SPECIFICATIONS		Test Conditions		Limits			
		Otherwise Unless Specified		- 40 °C to 85 °C			
Parameter	Symbol	V+ = 3 V, \pm 10 %, V _{IN} = 0.5 or 1.4 V ^e	Temp. ^a	Min. ^b	Typ. ^c	Max. ^b	Unit
Analog Switch	-						
Analan Cirnal Danaa ^d	V _{NO} , V _{NC} ,		Full	0		V+	v
Analog Signal Range ^d	V _{COM}		Fuii	0		v+	v
		V+ = 1.5 V, V _{COM} = 1.5 V, I _{NO} , I _{NC} = 10 mA	Room		5.3	7.0	
			Full			8.0	
	_	$V_{+} = 2.7 V$, $V_{COM} = 1.5 V$, I_{NO} , $I_{NC} = 10 mA$	Room		4.2	7.0	
On-Resistance	R _{ON}	$V_{+} = 2.7 V, V_{COM} = 2.7 V, I_{NO}, I_{NC} = 10 mA$			4.7		
			Full			8.0	
		V+ = 3.6 V, V _{COM} = 3.6 V, I _{NO} , I _{NC} = 10 mA	Room		5.5	7.0	Ω
	D		Full			8.0	
R _{ON} Flatness ^d	R _{ON}	V+ = 2.7 V, V _{COM} = 1.5 V, 2.7 V,	Room		0.6	2.0	
D Matchd	Flatness	I _{NO} , I _{NC} = 10 mA	Deem		0.1		
R _{ON} Match ^d	ΔR_{ON}		Room		0.1		
On Resistance (Shutdown)	R _{SHDN}	V+ = 3.6 V, V_{COM} = 1.7 V, I_{NO} , I_{NC} = 10 mA	Room Full		15	20	
	hier m					21	
Switch Off Leakage Current	I _{NO(off)} ,	V+ = 3.6 V, V _{NO} , V _{NC} = 0.3 V/3.3 V,	Room Full	- 2 - 10		2 10	
	I _{NC(off)}	$V_{COM} = 3.3 \text{ V}/0.3 \text{ V}$	Room	- 10		2	
	I _{COM(off)}	VCOM = 0.0 V/0.0 V	Full	- 2 - 10		10	nA
Channel-On Leakage			Room	- 2		2	
Current	I _{COM(on)}	V + = 3.6 V, V_{NO} , V_{NC} = V_{COM} = 0.3 V/3.3 V	Full	- 10		10	
Digital Control					1		
Input High Voltage	V _{INH}	V+ = 1.5 V		1.0			
Input High voltage	V INH	V+ = 2.7 V to 3.6 V	Full	1.4			v
Input Low Voltage	V _{INL}	V+ = 1.5 V	1 uii			0.4	v
		V+ = 2.7 V to 3.6 V				0.5	
Input Capacitance	C _{in}		Full		3.2		pF
Input Current	$I_{\rm INL}$ or $I_{\rm INH}$	V _{IN} = 0 or V+	Full	- 1		1	μΑ
Dynamic Characteristics		E		-			
Turn-On Time	t _{ON}		Room		39	69 70	
		V+ = 2.7 or 3.6 V, V _{NO} or V _{NC} = 1.5 V,	Full Room		0	76 39	
Turn-Off Time	t _{OFF}	$R_L = 50 $ Ω, $C_L = 35 $ pF	Full		9	39 41	ns
Break-Before-Make Time	t _d		Full	1		1	
Charge Injection ^d	Q _{INJ}	$C_L = 1 \text{ nF}, V_{GEN} = 0 \text{ V}, R_{GEN} = 0 \Omega$	Room		7		pC
Sharge injection	CINIZ	$R_L = 50 \ \Omega, \ C_L = 5 \ pF, \ f = 1 \ MHz$			- 77		60
Off-Isolation ^d	OIRR	$R_L = 50 \Omega, C_L = 5 pF, f = 100 MHz$	-		- 32		
		$R_L = 50 \ \Omega, \ C_L = 5 \ pF, \ f = 1 \ MHz$	Room				dB
Crosstalk ^{d, f}	X _{TALK}	$R_{L} = 50 \Omega, C_{L} = 5 \text{ pF}, T = 100 \text{ MHz}$	_		- 80		
		$h_{L} = 50.32, O_{L} = 5 \text{ pr}, I = 100 \text{ WHZ}$	Dearra		- 32		
N _O , N _C Off Capacitance ^d	C _{NO(off)}		Room		9		
-	C _{NC(off)}	f = 1 MHz	Room Room		7		pF
Channel-On Capacitance ^d	C _{NO(on)}	_			21		-
	Choopacitaice C _{NC(on)} Room		19		<u> </u>		

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SPECIFICATIONS	V+=3 V						
		Test Conditions Otherwise Unless Specified		Limits - 40 °C to 85 °C		°C	
Parameter	Symbol	V+ = 3 V, \pm 10 %, V _{IN} = 0.5 or 1.4 V ^e	Temp. ^a	Min. ^b	Typ. ^c	Max. ^b	Unit
Power Supply							
Power Supply Range	V+			1.5		3.6	V
Power Supply Current	l+	V + = 3.6 V, V_{IN} = 0 or V+, SHDN/ \overline{EN} = 0 V	Full		104	300	μA
	1+	V + = 3.6 V, V_{IN} = 0 or V+, SHDN/ \overline{EN} = V+	i uli		0.1	2	μΑ

Notes:

a. Room = 25 $^{\circ}$ C, Full = as determined by the operating suffix.

b. The algebraic convention whereby the most negative value is a minimum and the most positive a maximum, is used in this data sheet.

c. Typical values are for design aid only, not guaranteed nor subject to production testing.

d. Guarantee by design, not subjected to production test.

e. V_{IN} = input voltage to perform proper function.

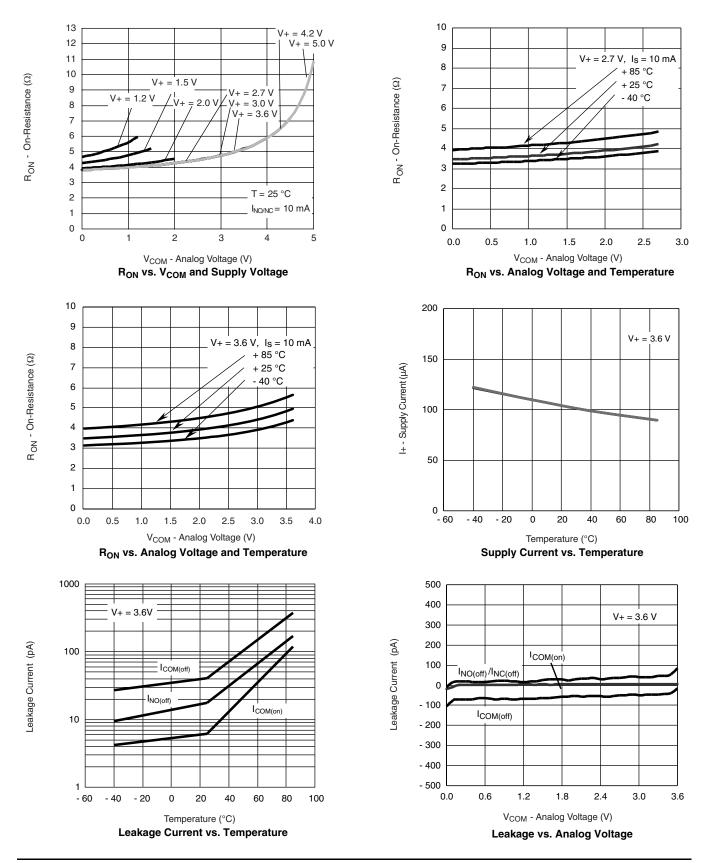
f. Crosstalk measured between channels.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



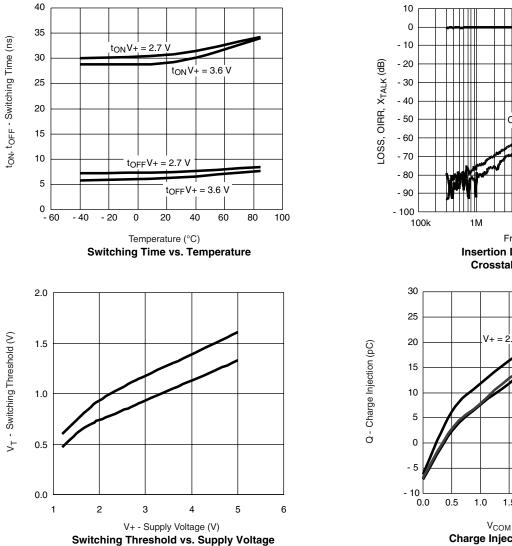
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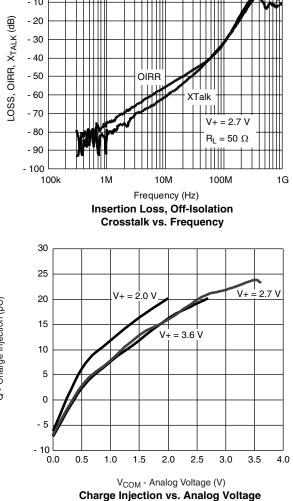
TYPICAL CHARACTERISTICS $T_A = 25$ °C, unless otherwise noted



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TYPICAL CHARACTERISTICS $T_A = 25$ °C, unless otherwise noted





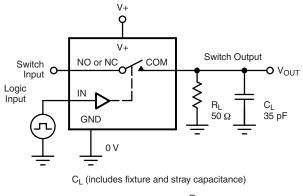
Loss

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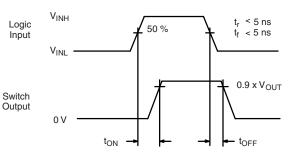


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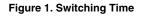
TEST CIRCUITS

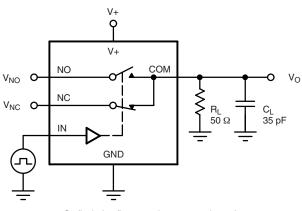


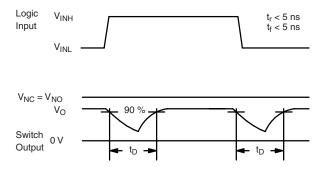




Logic "1" = Switch On Logic input waveforms inverted for switches that have the opposite logic sense.

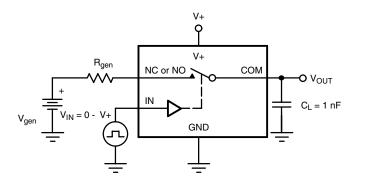


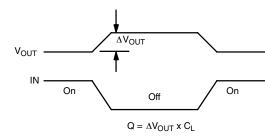




C_L (includes fixture and stray capacitance)

Figure 2. Break-Before-Make Interval



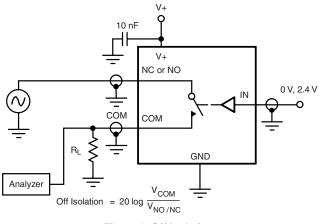


IN depends on switch configuration: input polarity determined by sense of switch.

Figure 3. Charge Injection

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TEST CIRCUITS



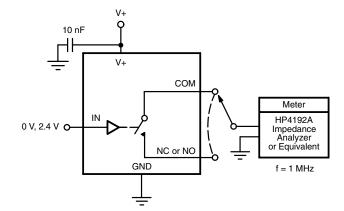


Figure 4. Off-Isolation

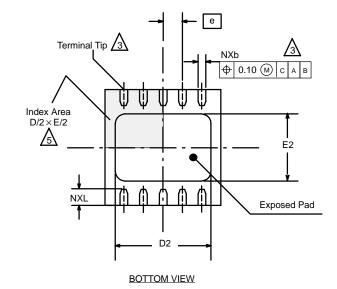
Figure 5. Channel Off/On Capacitance

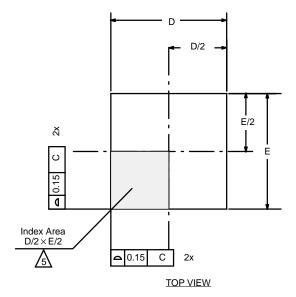
Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see http://www.vishay.com/ppg?74411.

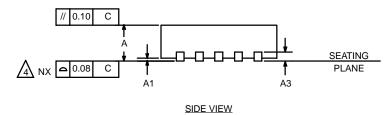




DFN-10 LEAD (3 X 3)







		MILLIMETERS			INCHES			
	Dim	Min	Nom	Max	Min	Nom	Max	
	Α	0.80	0.90	1.00	0.031	0.035	0.039	
and inches.	A1	0.00	0.02	0.05	0.000	0.001	0.002	
	A3	0.20 BSC			0.008 BSC			
l terminal and is measured terminal tip.	b	0.18	0.23	0.30	0.007	0.009	0.012	
d heat sink slug as well as the	D	3.00 BSC			0.118 BSC			
	D2	2.20	2.38	2.48	0.087	0.094	0.098	
r a mold or marked feature, it ndicated.	E	3.00 BSC			0.118 BSC			
luicaleu.	E2	1.49	1.64	1.74	0.059	0.065	0.069	
	е	0.50 BSC 0.020 BSC						
	L	0.30	0.40	0.50	0.012	0.016	0.020	
	*Use millir	neters as the	primary meas	surement.	•	•		
	ECN: S-42 DWG: 594		4, 29-Nov-04					

NOTES:

- 1. All dimensions are in millimeters and inches.
- 2. N is the total number of terminals.



<u>/5</u>

Dimension b applies to metallized terminal and is between 0.15 and 0.30 mm from terminal tip.

Coplanarity applies to the exposed heat sink slug as well as the terminal.

The pin #1 identifier may be either a mold or marked feature, it must be located within the zone iindicated.



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